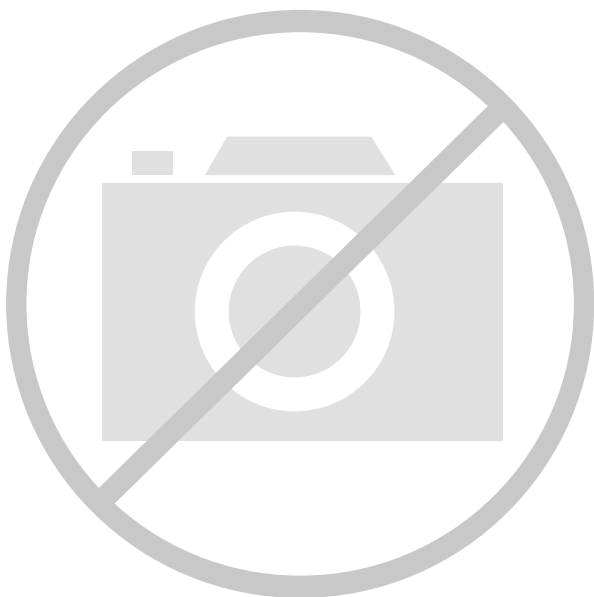




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Notes for CMOS Devices

1. Precaution against ESD for semiconductors

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

2. Handling of unused input pins for CMOS

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

3. Status before initialization of MOS devices

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

Regional Information

Some information contained in this document may vary from country to country. Before using any NEC product in your application, please contact the NEC office in your country to obtain a list of authorized representatives and distributors. They will verify:

- Device availability
- Ordering information
- Product release schedule
- Availability of related technical literature
- Development environment specifications (for example, specifications for third-party tools and components, host computers, power plugs, AC supply voltages, and so forth)
- Network requirements

In addition, trademarks, registered trademarks, export restrictions, and other legal issues may also vary from country to country.

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1.4 Pin Groups 3x: Pins supplied by BVDD

3A: (CMOS)

- PCM0-3, PCS0-1, PCT0-1, PCT4, PCT6 (FG3-L)

3D: (SHMT3)

- PDL0-13 (FG3-L)

1.5 Pin Groups 4: Pins supplied by AVREF0

4: (CMOS)

- P70-79 (FE3-L)
- P70-711 (FF3-L)
- P70-715 (FG3-L)

1.6 Pin Groups 6: Pins supplied by EVDD

- RESET (SHMT2)
- IC, FLMD0

1.7 Pin Groups 7: Pins supplied by VRO

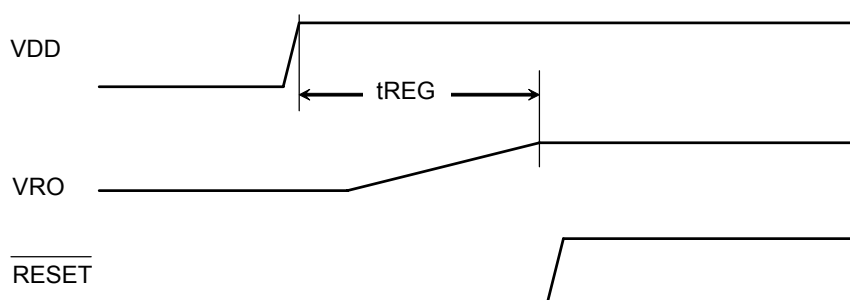
- X1, X2, XT1, XT2

2.4 Voltage Regulator Characteristics

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD, VSS = EVSS = AVSS = 0V))

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage	VDD		3.5		5.5	V
		Limited function see '2.3 Operating condition'	3.3			V
Output voltage	VRO			2.5		V
Output voltage stabilization time	t _{REG} ^{Note}	After VDD reaches voltage range min. 3.3V To connect C=4.7uF on REGC terminal			1	ms

Note: In case of non-POC device, be sure to start VDD in the state of $\overline{\text{RESET}} = \text{VSS} = 0\text{V}$.
For POC devices there is no need to control external $\overline{\text{RESET}}$ terminal. For decives with POC function the internal $\overline{\text{RESET}}$ signal will automatically controlled until VRO is stable.



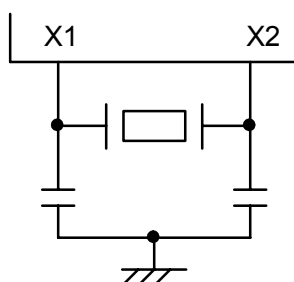
2.5 Clock Generator Circuit

2.5.1 Main System Clock Oscillation Circuit Characteristics

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V)

Resonator	Recommended Circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Crystal / Ceramic resonator	Refer to figure below	Oscillator frequency (fx) ^{Note1}		4		16	MHz
		Oscillation stabilization time ^{Note2}	After STOP mode	54 ^{Note4}	Note3		μs
			After IDLE2 mode	54 ^{Note4}	Note3		μs

- Notes:**
1. Indicates only oscillation circuit characteristics. Refer to '2.7 AC Characteristics' for CPU operation clock.
 2. Time required to stabilize oscillation after VDD reaches oscillator voltage range MIN. 3.3V
 3. Depends on the setting of the oscillation stabilization time select register (OSTS)
 4. Minimum time required to stabilize flash. Time has to be secured by setting the oscillation stabilization time select register (OSTS)



2.5.4 PLL Characteristics

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,
C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input frequency	f_x		4		16	MHz
	f_{PLLI}	Note1	3		6	MHz
Output frequency	f_{xx}		10		20	MHz
Lock time	tPLL	After VDD reaches voltage range min. 3.3V			800	μs
Output period jitter Note2	tpj	Peak to peak			2.0	ns

Notes: 1. The input of the PLL (f_{PLLI}) can be set to f_x , $f_x/2$, or $f_x/4$. The divider is set through an option byte in the code flash memory.

2. Not tested in production.

16 2.6.3 Power supply current

2.6.3.1 FF3-L μ PD70F3615, μ PD70F3616, μ PD70F3617, μ PD70F3618, μ PD70F3619

(a) Absolute values

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,

C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V^{Note1)}

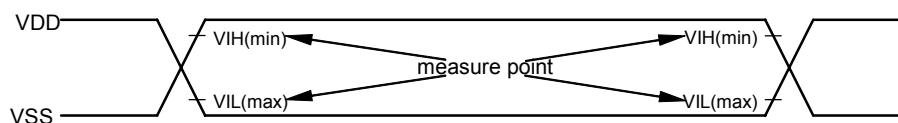
Mode	Symbol	Condition				TYP.	MAX.			Unit
							(A)	(A1)	(A2)	
Operating mode Note2	IDD1	All peripherals running	Peripheral: f _{xx} PRSI option: 0	PLL: ON 16MHz ≤ f _{xx} ≤ 20MHz	f _{xx} =10MHz f _x =5MHz	16	24			mA
					f _{xx} =20MHz f _x =10MHz	25	35			mA
				PLL: OFF 4MHz ≤ f _{xx} ≤ 16MHz	f _{xx} =8MHz 8MHz Internal-OSC ^{Note3}	12	19			mA
					f _{xx} =16MHz f _x =16MHz	20	28			mA
			Peripheral: f _{xx} /2 PRSI option: 1	PLL: ON 10MHz ≤ f _{xx} ≤ 20MHz	f _{xx} =20MHz f _x =10MHz	22	32			mA
		All peripherals stopped	Peripheral: f _{xx} PRSI option: 0	PLL: ON 16MHz ≤ f _{xx} ≤ 20MHz	f _{xx} =10MHz f _x =5MHz	13	-			mA
					f _{xx} =20MHz f _x =10MHz	21				mA
				PLL: OFF 4MHz ≤ f _{xx} ≤ 16MHz	f _{xx} =8MHz 8MHz Internal-OSC ^{Note3}	11				mA
					f _{xx} =16MHz f _x =16MHz	18				mA
			Peripheral: f _{xx} /2 PRSI option: 1	PLL: ON 10MHz ≤ f _{xx} ≤ 20MHz	f _{xx} =20MHz f _x =10MHz	21				mA

Mode	Symbol	Condition				TYP.	MAX.			Unit
							(A)	(A1)	(A2)	
HALT mode	IDD2	All peripherals running	Peripheral: f_{xx} PRSI option: 0	PLL: ON $16\text{MHz} \leq f_{xx} \leq 20\text{MHz}$	$f_{xx}=10\text{MHz}$ $f_x=5\text{MHz}$	10	15			mA
					$f_{xx}=20\text{MHz}$ $f_x=10\text{MHz}$	17	25			mA
			Peripheral: f_{xx} PRSI option: 0	PLL: OFF $4\text{MHz} \leq f_{xx} \leq 16\text{MHz}$	$f_{xx}=8\text{MHz}$ 8MHz Internal-OSC ^{Note3}	7	11			mA
					$f_{xx}=16\text{MHz}$ $f_x=16\text{MHz}$	12	18			mA
			Peripheral: $f_{xx}/2$ PRSI option: 1	PLL: ON $10\text{MHz} \leq f_{xx} \leq 20\text{MHz}$	$f_{xx}=20\text{MHz}$ $f_x=10\text{MHz}$	14	21			mA
		All peripherals stopped	Peripheral: f_{xx} PRSI option: 0	PLL: ON $16\text{MHz} \leq f_{xx} \leq 20\text{MHz}$	$f_{xx}=10\text{MHz}$ $f_x=5\text{MHz}$	7	-			mA
					$f_{xx}=20\text{MHz}$ $f_x=10\text{MHz}$	12				mA
				PLL: OFF $4\text{MHz} \leq f_{xx} \leq 16\text{MHz}$	$f_{xx}=8\text{MHz}$ 8MHz Internal-OSC ^{Note3}	5				mA
					$f_{xx}=16\text{MHz}$ $f_x=16\text{MHz}$	9				mA
			Peripheral: $f_{xx}/2$ PRSI option: 1	PLL: ON $10\text{MHz} \leq f_{xx} \leq 20\text{MHz}$	$f_{xx}=20\text{MHz}$ $f_x=10\text{MHz}$	11				mA

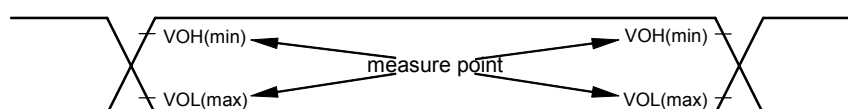
Mode	Symbol	Condition			TYP.	MAX.			Unit
						(A)	(A1)	(A2)	
IDLE1 mode	IDD3	Peripheral (TAA, UARTD) running	PLL: OFF 4MHz≤f _{xx} ≤16MHz Note7	f _{xx} =5MHz f _x =5MHz	1.4	2.2	2.5	2.8	mA
				f _{xx} =12MHz f _x =12MHz	2.0	3.1	3.4	3.7	mA
				f _{xx} =16MHz f _x =16MHz	2.4	3.6	3.9	4.2	mA
			fxx=8MHz, 8MHz Internal-OSC ^{Note3}		1.5	2.3	2.6	2.9	mA
		All peripherals stopped	PLL: OFF 4MHz≤f _{xx} ≤16MHz Note7	f _{xx} =5MHz f _x =5MHz	1.2	-			mA
				f _{xx} =12MHz f _x =12MHz	1.4				mA
				f _{xx} =16MHz f _x =16MHz	1.6				mA
			fxx=8MHz, 8MHz Internal-OSC ^{Note3}		1.1				mA
IDLE2 mode	IDD4	PLL: OFF 4MHz≤f _{xx} ≤16MHz Note7		f _{xx} =5MHz f _x =5MHz	0.4	0.7	0.9	1.1	mA
				f _{xx} =12MHz f _x =12MHz	0.7	1.0	1.2	1.5	mA
				f _{xx} =16MHz f _x =16MHz	0.8	1.2	1.4	1.7	mA
		fxx=8MHz, 8MHz Internal-OSC ^{Note3}			0.2	0.5	0.7	1.0	mA
SUB operating mode ^{Note5}	IDD5	Crystal resonator (fxt = 32,768kHz)			80	400	-	-	μA
		RC resonator (fxt=20kHz) ^{Note6}			80	400	600	850	μA
		240 kHz Internal-OSC (SubOSC stopped)			220	1000	1200	1450	μA
SubIDLE mode ^{Note3,5}	IDD6	Crystal resonator (fxt = 32,768kHz)			20	190	-	-	μA
		RC resonator (fxt=20kHz) ^{Note6}			40	220	420	670	μA
		240kHz Internal-OSC (SubOSC stopped)			25	180	380	630	μA
STOP mode ^{Note3,4}	IDD7	POC stop	240kHz Internal-OSC stop		7.5	80	280	530	μA
			240kHz Internal-OSC working		15.5	95	295	545	μA
		POC work	240kHz Internal-OSC stop		10.5	85	285	535	μA
			240kHz Internal-OSC working		18.5	100	300	550	μA

2.7 AC Characteristics

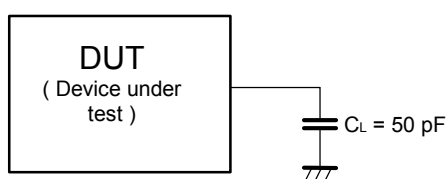
AC test Input measurement points (VDD, AVREF0, EVDD)



AC test output measurement points



Load conditions



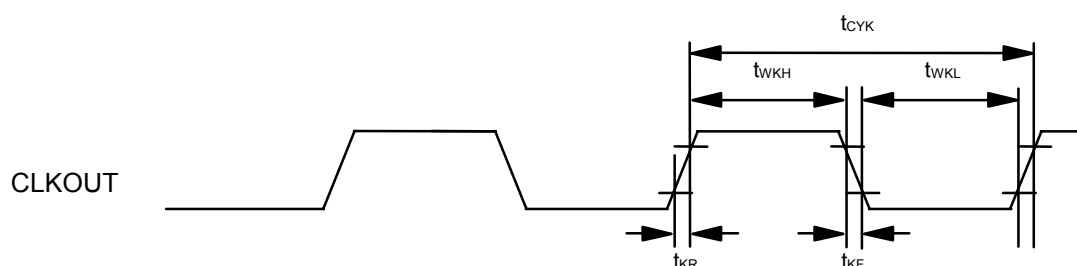
Caution: If the load capacitance exceeds 50pF due to the circuit configuration, reduce the load capacitance of the device to 50pF or less by inserting a buffer or by some other means.

2.7.1 CLKOUT Output Timing

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,
VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
Output cycle	tCYK		50ns	80μs	
High level width	tWKH	VDD = EVDD = 4.0V ~ 5.5V	tCYK/2-13		ns
		VDD = EVDD = 3.5V ~ 5.5V	tCYK/2-15		
Low level width	tWKL	VDD = EVDD = 4.0V ~ 5.5V	tCYK/2-13		ns
		VDD = EVDD = 3.5V ~ 5.5V	tCYK/2-15		
Rise time	tKR	VDD = EVDD = 4.0V ~ 5.5V		13	ns
		VDD = EVDD = 3.5V ~ 5.5V		15	
Fall time	tKF	VDD = EVDD = 4.0V ~ 5.5V		13	ns
		VDD = EVDD = 3.5V ~ 5.5V		15	

CLKOUT output timing



2.7.2 RESET, Interrupt, ADTRG Timing

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,
VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
RESET input low level width	tWRSL	analog filter	250			ns
NMI input high level width	tWNIH	analog filter	250			ns
NMI input low level width	tWNIL	analog filter	250			ns
INTPn ^{Note1} input high level width	tWITH	analog filter ,n=0-8	250			ns
		digital filter ,n=3	Note2			ns
INTPn ^{Note1} input low level width	tWITL	analog filter ,n=0-8	250			ns
		digital filter ,n=3	Note2			ns

Notes: 1. ADTRG is same spec (P03/INTP0/ADTRG). $\overline{\text{DRST}}$ is same spec (P05/INTP2/ $\overline{\text{DRST}}$)
2. 2Tsamp+20 or 3Tsamp+20 ("Tsamp" is Noise reject sampling clock (NF macro))

Remarks: 1. The above minimum values show pulse widths that are surely detected as an effective edge. An effective may also be detected even if the input pulse width is less than the above minimum specification.
2. RESET, NMI, INTPn, ADTRG and $\overline{\text{DRST}}$ have analog noise filter. The typical filter time is typ=60ns.

2.7.3 Key Return Timing

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,
VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
KRn input high level width	tWKRH	analog filter ,n=0-7	250			ns
KRn input low level width	tWKRL	analog filter ,n=0-7	250			ns

Remarks: 1. The above minimum values show pulse widths that are surely detected as an effective edge. An effective may also be detected even if the input pulse width is less than the above minimum specification.
2. KRn inputs have analog noise filter. The typical filter time is typ=60ns.

2.7.4 Timer Timing

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,
VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
TI input high level width	tTIH	TIAA00-01,10-11,20-21,30-31,40-41 ^{Note1}	250			ns
TI input low level width	tTIL	TIAA00-01,10-11,20-21,30-31,40-41 ^{Note1}	250			ns
TO output cycle	tTCYK	TIAA00-01,10-11,20-21,30-31, 40-41 ^{Note1}			10	MHz

Notes: 1. Except for the external trigger and external event function.

Remarks: 1. The above minimum values show pulse widths that are surely detected as an effective edge. An effective may also be detected even if the input pulse width is less than the above minimum specification.
2. TIAAn inputs have analog noise filter. The typical filter time is typ=60ns.

2.7.5 CSI Timing

(a) Master mode

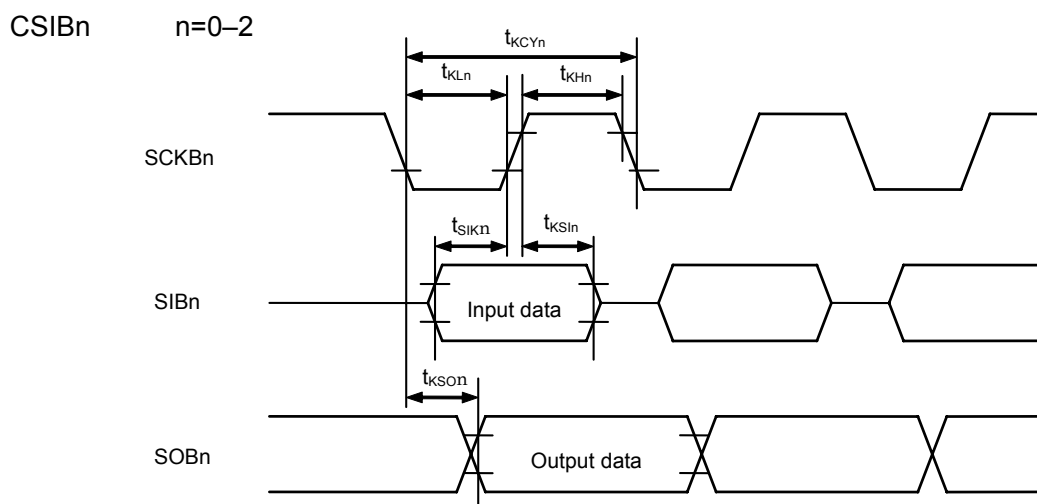
(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,
VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCKBn cycle time	tKCY1		125		ns
SCKBn high level width	tKH1		tKCY1/2-15		ns
SCKBn low level width	tKL1		tKCY1/2-15		ns
SIBn setup time (to SCKBn)	tSIK1		30		ns
SIBn hold time (from SCKBn)	tKSI1		25		ns
Delay time from SCKBn to SOBn	tKSO1			25	ns

(b) Slave mode

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,
VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCKBn cycle time	tKCY1		200		ns
SCKBn high level width	tKH1		90		ns
SCKBn low level width	tKL1		90		ns
SIBn setup time (to SCKBn)	tSIK1		50		ns
SIBn hold time (from SCKBn)	tKSI1		50		ns
Delay time from SCKBn to SOBn	tKSO1			50	ns



2.7.6 UART Timing

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,
VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					1.5	Mbps
ASCK0 frequency					10	MHz

2.7.7 IIC Timing

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,
VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

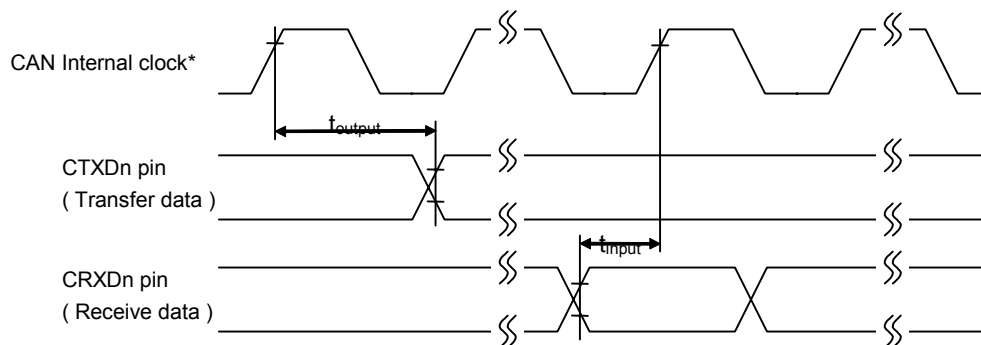
Parameter		Symbol	Normal mode		High-speed mode		Unit
			min.	max.	min.	max.	
SCL00 clock frequency		fCLK	0	100	0	400	kHz
Bus-free time (between stop/start conditions)		tBUF	4.7		1.3		μs
Hold time ^{Note1}		tHD:STA	4.0		0.6		μs
SCL00 clock low-level width		tLOW	4.7		1.3		μs
SCL00 clock high-level width		tHIGH	4.0		0.6		μs
Setup time for start/restart conditions		tSU:STA	4.7		0.6		μs
Data hold time	CBUS compatible master	tHD:DAT	5.0				μs
	IIC mode		0 ^{Note2}		0 ^{Note2}	0.9 ^{Note3}	μs
Data setup time		tSU:DAT	250		100 ^{Note4}		ns
SDA00 and SCL00 signal rise time		tR		1000	20+0.1Cb	300	ns
SDA00 and SCL00 signal fall time		tF		300	20+0.1Cb	300	ns
Stop condition setup time		tSU:STO	4.0		0.6		μs
Pulse width with spike suppressed by input filter		tSP			0	50	ns
Capacitance load of each bus line		Cb		400		400	pF

- Notes:**
1. At the start condition, the first clock pulse is generated after the hold time
 2. The system requires a minimum of 300ns hold time Internally for the SDA signal (at VIH-min. of SCL00 signal)
In order to occupy the undefined area at the falling edge of SCL00.
 3. If the system does not extend the SCL00 signal low hold time (tLOW), only the maximum data hold time (tHD:DAT) needs to be satisfied.
 4. The high-speed-mode IIC bus can be used In a normal-mode IIC bus system.
In this case, set the high-speed-mode IIC bus so that It meets the following conditions.
- If the system does not extend the SCL00 signal's low state hold time:
SU:DAT?250ns
- If the system extends the SCL00 signal's low state hold time:
Transmit the following data bit to the SDA00 line prior to releasing the SCL00 line
(tRmax.+tSU:DAT=1000+250=1250ns: Normal mode IIC bus specification).
 5. Cb: Total capacitance of one bus line (unit: pF)

2.7.8 CAN Timing

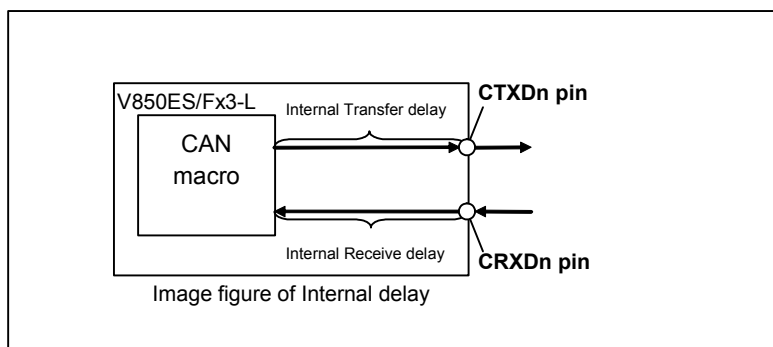
(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade,
VDD = EVDD = 3.5 to 5.5V, AVREF0 = 3.5 to 5.5V, VSS = EVSS = AVSS = 0V, CL=50pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					1	Mbps
Internal delay time					100	ns



Internal delay time (t_{NODE}) = Internal Transfer Delay(t_{output}) + Internal Receive Delay(t_{input})

*) CAN Internal clock (f_{CAN}): CAN baud rate clock



2.8 A/D Converter

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 3.5 to 5.5V, AVREF0 = 4.0 to 5.5V, VSS = EVSS = AVSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.		Unit
					(A),(A1)	(A2)	
Resolution					10		bit
Overall error ^{Note1}		4.0V ≤ AVREF0 < 5.5V		±0.15	±0.3	±0.35	%FSR
Conversion time	tCONV		3.10		16		μs
Stabilization time	tSTA	After ADA0PS bit = 0 -> 1	2				μs
Recovery time for power down mode	tDPU		1				μs
Zero-scale error ^{Note1}	ZSE				±0.3	±0.35	%FSR
Full-scale error ^{Note1}	FSE				±0.3	±0.35	%FSR
Integral non-linearity error ^{Note2}	INL				±2.5		LSB
Differential non-linearity error ^{Note2}	DNL				±1.5		LSB
Analog input voltage	VIAN		AVSS		AVREF0		V
Analog input equivalent circuit capacitance ^{Note3,4}	CINA				6.19		pF
Analog input equivalent circuit resistance ^{Note3}	RINA				2.55		kΩ
AVREF0 current	IAREF0	A/D operating		4	7		mA
		A/D operation stop		1	10		μA
Conversion result when using Diagnostic function		AVREF0 conversion	3FC		3FF		HEX
		AVSS conversion	000		003		HEX

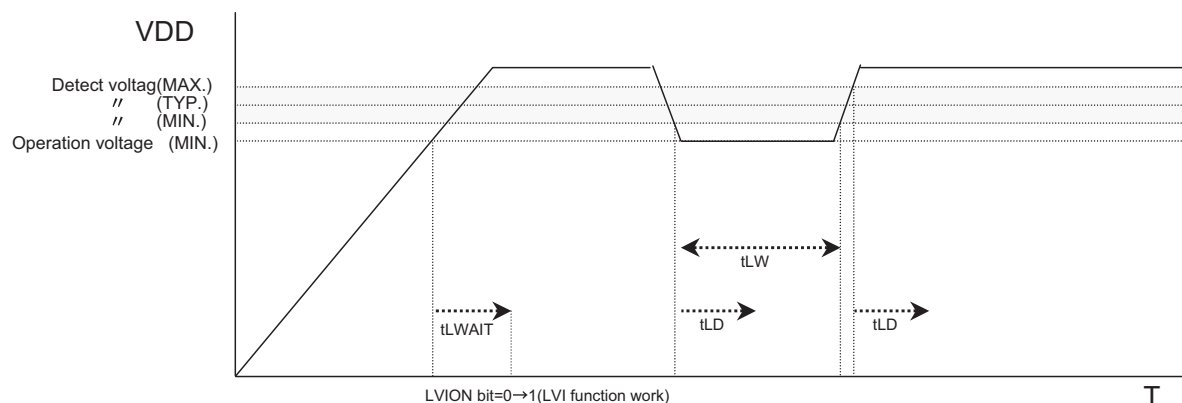
- Notes:**
1. Overall error excluding quantization error (±0.05%FSE). It is indicated as a ratio to the full-scale value.
 2. Excluding quantization error (±1/2 LSB)
 3. Reference value. Not tested in production.
 4. Does not include input/output capacitance CIO

2.10 LVI

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 3.3 to 5.5V, AVREF0 = 3.3 to 5.5V, VSS = EVSS = AVSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detect voltage	VLVI0		3.8	4.0	4.2	V
	VLVI1		3.5	3.7	3.9	V
Response time ^{Note1}	tLD	After VDD reaches VLVI0/1(max). After VDD drop VLVI0/1(min).		0.2	2.0	ms
VDD minimum width	tLW		0.2			ms
Reference voltage stabilization wait time ^{Note2}	tLWAIT	After VDD reaches 3.3V. After LVION bit (LVIM.bit7) = 0->1		0.1	0.2	ms

- Notes:** 1. From detect voltage to occurrence interrupt/reset signal
2. If POC functionality is available, the wait time is not needed.

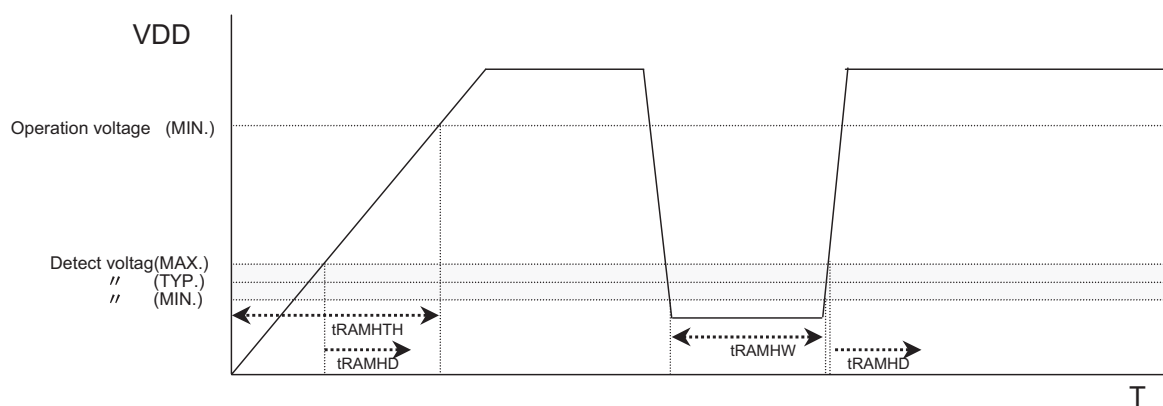


2.11 RAM Retention Flag

(Ta = -40 to +85°C for (A)-Grade, Ta = -40 to +110°C for (A1)-Grade, Ta = -40 to +125°C for (A2)-Grade, C=4.7uF, VDD = EVDD = 1.9 to 5.5V, VSS = EVSS = AVSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detect voltage	VRAMH		1.9	2.0	2.1	V
Supply voltage rise time	tRAMHTH	From VDD=0V to VDD=3.3V	0.002		1800	ms
Response time ^{Note1}	tRAMHD	After VDD reaches 2.1V.		0.2	2.0	ms
VDD minimum width	tRAMHW		0.2			ms

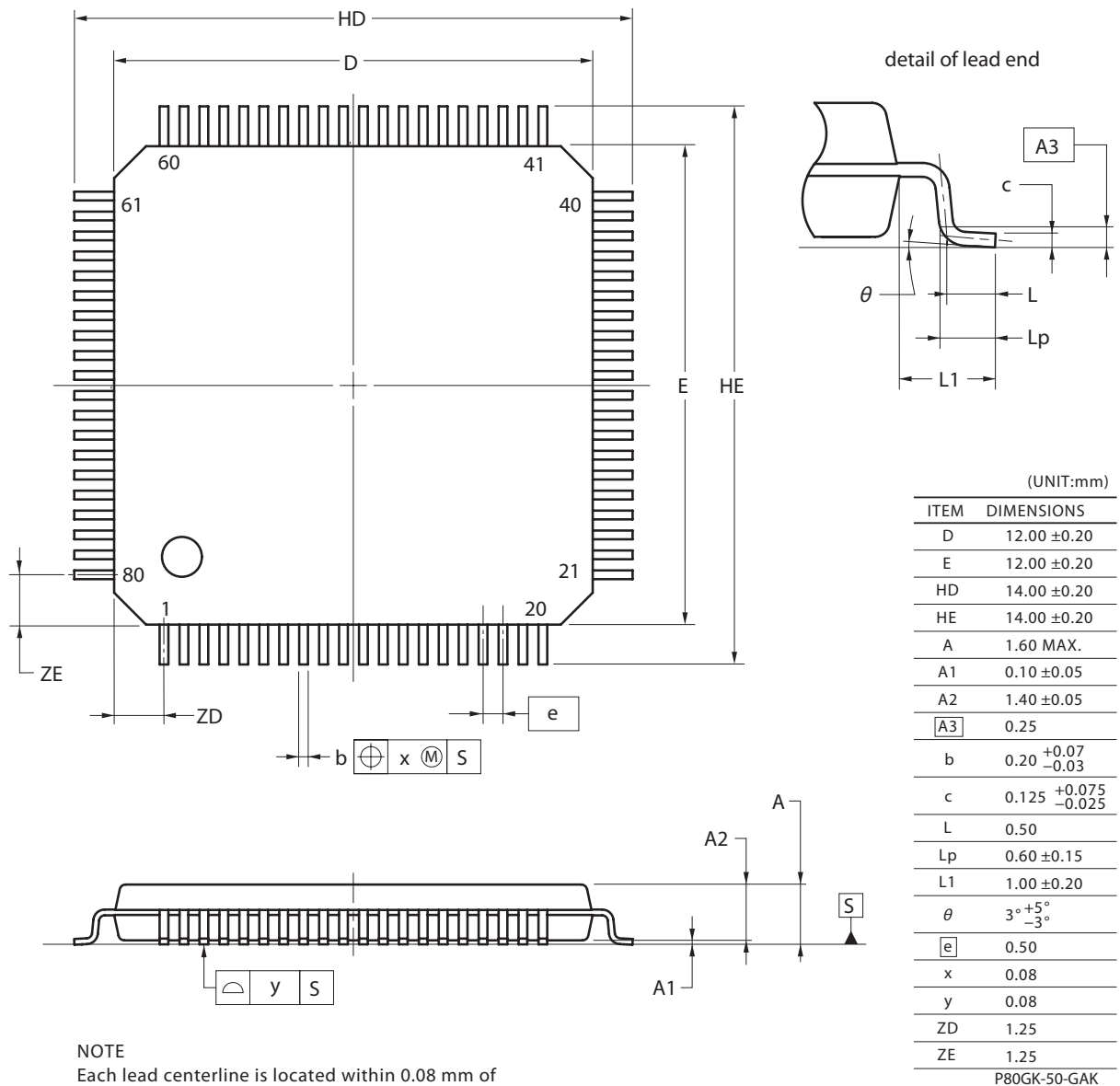
- Notes:** 1. From detect voltage to set RAMFbit (RAMS.bit0)



3. Package

3.1 Package Dimension

80-PIN PLASTIC LQFP (FINE PITCH) (12x12)



NOTE

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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4. Change History

Version	Chapter	Comment
V1.0		Initial release

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